

TOSHIBA

2SC3265

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

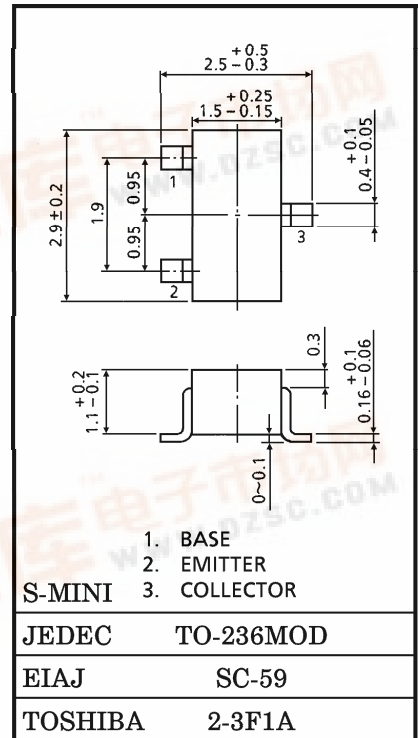
2SC3265

LOW FREQUENCY POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

- High DC Current Gain : $h_{FE}(1) = 100\sim320$
- Low Saturation Voltage : $V_{CE(sat)} = 0.4\text{ V (Max.)}$
($I_C = 500\text{ mA}$, $I_B = 20\text{ mA}$)
- Complementary to 2SA1298

Unit in mm

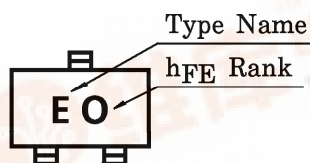


MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Base Current	I_B	160	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

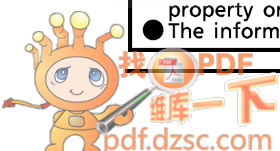
Weight : 0.012 g

MARKING



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 30\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	25	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{ mA}, I_C = 0$	5	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = 1\text{ V}, I_C = 800\text{ mA}$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{ mA}, I_B = 20\text{ mA}$	—	—	0.4	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}$	0.5	—	0.8	V
Transition Frequency	f_T	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	13	—	pF

Note : $h_{FE(1)}$ Classification O : 100~200, Y : 160~320

